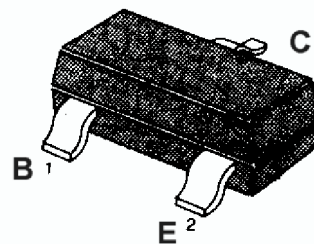


APPLICATION: Low Frequency Amplifier Applications.

MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CBO}	40	V
Collector-emitter voltage	V _{CEO}	25	V
Emitter-base voltage	V _{EBO}	6	V
Collector current	I _C	1500	mA
Collector Power Dissipation	P _C	200	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	- 55~150	°C

SOT-23


1.Base 2. Emitter 3. Collector

ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h _{FE}	100		500		V _{CE} = 1V, I _C = 100mA
Collector Cut-off Current	I _{CBO}			0.1	μA	V _{CB} = 35V, I _E =0
Emitter Cut-off Current	I _{EBO}			0.1	μA	V _{EB} = 6V, I _C =0
Collector-Base Breakdown Voltage	BV _{CBO}	40			V	I _C = 0.1mA, I _E =0
Collector-Emitter Breakdown Voltage	BV _{CEO}	25			V	I _C = 2mA, I _B =0
Emitter-Base Breakdown Voltage	BV _{EBO}	6			V	I _E = 0.1mA, I _C =0
Base-Emitter Voltage	V _{BE}		0.66	1	V	V _{CE} = 1V, I _C = 10mA
Collector-Emitter Saturation Voltage	V _{CE(sat)}		0.28	0.5	V	I _C = 800mA, I _B = 80mA
Gain bandwidth product	f _T	50	190		MHz	I _C = 50mA, V _{CE} = 10V
Common Base Output Capacitance	C _{ob}		9	20	PF	V _{CB} = 10V, I _E =0, f = 1MHz

h_{FE} Classification And Marking

Print Mark

EY

 h_{FE}

160~320

